

# Zoran Ikonic

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9405199/publications.pdf>

Version: 2024-02-01

155  
papers

3,927  
citations

159585

30  
h-index

123424

61  
g-index

156  
all docs

156  
docs citations

156  
times ranked

2695  
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced GeSn Microdisk Lasers Directly Released on Si. <i>Advanced Optical Materials</i> , 2022, 10, 2101213.	7.3	22
2	Prospects of temperature performance enhancement through higher resonant phonon transition designs in GaAs-based terahertz quantum-cascade lasers. <i>New Journal of Physics</i> , 2022, 24, 033047.	2.9	7
3	The effect of interface roughness on spectral efficiency of thermophotovoltaics with multi-layer filters. <i>Optik</i> , 2022, 257, 168663.	2.9	0
4	Design optimization of tensile-strained SiGeSn/GeSn quantum wells at room temperature. <i>Journal of Applied Physics</i> , 2021, 129, 123102.	2.5	5
5	Thermoelectric Efficiency of Epitaxial GeSn Alloys for Integrated Si-Based Applications: Assessing the Lattice Thermal Conductivity by Raman Thermometry. <i>ACS Applied Energy Materials</i> , 2021, 4, 7385-7392.	5.1	13
6	Design considerations of intra-step SiGeSn/GeSn quantum well electroabsorption modulators. <i>Journal of Applied Physics</i> , 2021, 130, 153103.	2.5	2
7	Ultra-low-threshold continuous-wave and pulsed lasing in tensile-strained GeSn alloys. <i>Nature Photonics</i> , 2020, 14, 375-382.	31.4	145
8	Dual resonance phononâ€“photonâ€“phonon terahertz quantum-cascade laser: physics of the electron transport and temperature performance optimization. <i>Optics Express</i> , 2020, 28, 38788.	3.4	13
9	Femtosecond pulsed laser deposited Er <sup>3+</sup> -doped zinc-sodium tellurite glass on Si: Thin-film structural and photoluminescence properties. <i>AIP Advances</i> , 2019, 9, .	1.3	2
10	Impact of tensile strain on low Sn content GeSn lasing. <i>Scientific Reports</i> , 2019, 9, 259.	3.3	49
11	Density matrix superoperator for periodic quantum systems and its application to quantum cascade laser structures. <i>AIP Advances</i> , 2019, 9, .	1.3	9
12	Ultra-Low Threshold cw Lasing in Tensile Strained GeSn Microdisk Cavities. , 2019, , .		0
13	Frequency Tuning Range Control in Pulsed Terahertz Quantum-Cascade Lasers: Applications in Interferometry. <i>IEEE Journal of Quantum Electronics</i> , 2018, 54, 1-8.	1.9	9
14	Investigation of carrier confinement in direct bandgap GeSn/SiGeSn 2D and 0D heterostructures. <i>Scientific Reports</i> , 2018, 8, 15557.	3.3	36
15	GeSn/SiGeSn Heterostructure and Multi Quantum Well Lasers. <i>ACS Photonics</i> , 2018, 5, 4628-4636.	6.6	84
16	Correlation of Bandgap Reduction with Inversion Response in (Si)GeSn/High-k/Metal Stacks. <i>ACS Applied Materials &amp; Interfaces</i> , 2017, 9, 9102-9109.	8.0	7
17	SiGeSn Ternaries for Efficient Group IV Heterostructure Light Emitters. <i>Small</i> , 2017, 13, 1603321.	10.0	40
18	Infinite-Period Density-Matrix Model for Terahertz-Frequency Quantum Cascade Lasers. <i>IEEE Transactions on Terahertz Science and Technology</i> , 2017, 7, 368-377.	3.1	16

#	ARTICLE	IF	CITATIONS
19	Design of a high-speed germanium-tin absorption modulator at mid-infrared wavelengths. , 2017, , .		6
20	Short-wave infrared LEDs from GeSn/SiGeSn multiple quantum wells. Optica, 2017, 4, 185.	9.3	90
21	Origin of terminal voltage variations due to self-mixing in terahertz frequency quantum cascade lasers. Optics Express, 2016, 24, 21948.	3.4	10
22	Process modules for GeSn nanoelectronics with high Sn-contents. , 2016, , .		0
23	Low Temperature Deposition of High-k/Metal Gate Stacks on High-Sn Content (Si)GeSn-Alloys. ACS Applied Materials & Interfaces, 2016, 8, 13133-13139.	8.0	18
24	Terahertz frequency quantum cascade lasers: Optical feedback effects and applications. , 2016, , .		1
25	Electronic structure of (Si)GeSn and its tuning via incorporation of carbon. , 2016, , .		0
26	Design considerations for GaN/AlN based unipolar (opto-)electronic devices, and interface quality aspects. , 2016, , .		0
27	Magnetic field effects on THz quantum cascade laser: A comparative analysis of three and four quantum well based active region design. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 81, 275-280.	2.7	5
28	Terahertz quantum cascade laser bandwidth prediction. , 2015, , .		0
29	Lasing in direct-bandgap GeSn alloy grown on Si. Nature Photonics, 2015, 9, 88-92.	31.4	1,016
30	Direct Bandgap Group IV Epitaxy on Si for Laser Applications. Chemistry of Materials, 2015, 27, 4693-4702.	6.7	122
31	GeSn for nanoelectronic and optical applications. , 2015, , .		3
32	A QCL model with integrated thermal and stark rollover mechanisms. , 2014, , .		0
33	Epitaxy and photoluminescence studies of high quality GeSn heterostructures with Sn concentrations up to 13 at.%. , 2014, , .		1
34	Si-Ge-Sn heterostructures: Growth and applications. , 2014, , .		0
35	Strain engineering for direct bandgap GeSn alloys. , 2014, , .		1
36	Genetic algorithm applied to the optimization of quantum cascade lasers with second harmonic generation. Journal of Applied Physics, 2014, 115, 053712.	2.5	4

#	ARTICLE	IF	CITATIONS
37	Importance of Polaronic Effects for Charge Transport in CdSe Quantum Dot Solids. Journal of Physical Chemistry Letters, 2014, 5, 1335-1340.	4.6	21
38	Optimizing optical nonlinearities in GaInAs/AlInAs quantum cascade lasers. Nuclear Technology and Radiation Protection, 2014, 29, 10-16.	0.8	5
39	Tensely strained GeSn alloys as optical gain media. Applied Physics Letters, 2013, 103, .	3.3	63
40	Design and performance of a prototype mesa-geometry Ge-on-Si single-photon avalanche diode detector at 1310 nm and 1550 nm wavelengths. , 2013, , .		0
41	Surface acoustic wave modulation of quantum cascade lasers. , 2013, , .		1
42	Comparative study of intersubband absorption in AlGaIn/GaN and AlInN/GaN superlattices: Impact of material inhomogeneities. Physical Review B, 2013, 88, .	3.2	28
43	Simulated effect of epitaxial growth variations on THz emission of SiGe/Ge quantum cascade structures. , 2013, , .		0
44	Plasmonic Modulators for Near-Infrared Photonics on a Silicon-on-Insulator Platform. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 4601708-4601708.	2.9	7
45	Band engineering and growth of tensile strained Ge/(Si)GeSn heterostructures for tunnel field effect transistors. Applied Physics Letters, 2013, 102, .	3.3	131
46	Strong heavy-to-light hole intersubband absorption in the valence band of carbon-doped GaAs/AlAs superlattices. Journal of Applied Physics, 2013, 113, 053103.	2.5	2
47	Self-mixing effect in THz quantum cascade lasers: Applications in sensing and imaging. , 2013, , .		1
48	Swept-frequency feedback interferometry using terahertz frequency QCLs: a method for imaging and materials analysis. Optics Express, 2013, 21, 22194.	3.4	91
49	Ge-on-Si Single-Photon Avalanche Diode Detectors: Design, Modeling, Fabrication, and Characterization at Wavelengths 1310 and 1550 nm. IEEE Transactions on Electron Devices, 2013, 60, 3807-3813.	3.0	116
50	Heavy-to-light hole intersubband absorption in the valence band of GaAs/AlAs heterostructures. Materials Research Society Symposia Proceedings, 2013, 1509, 1.	0.1	0
51	Influence of absorber layer dopants on performance of Ge/Si single photon avalanche diodes. Journal of Applied Physics, 2013, 113, 144508.	2.5	0
52	Optimum strain configurations for carrier injection in near infrared Ge lasers. Journal of Applied Physics, 2012, 111, .	2.5	39
53	Designing short tapered waveguide adapters for Ge lasers and Ge/SiGe modulators integrated with SOI waveguides. , 2012, , .		0
54	A CMOS compatible metallised nanofocusing coupler. , 2012, , .		0

#	ARTICLE	IF	CITATIONS
55	Development of quantum cascade laser simulation software. , 2012, , .		1
56	The direct and indirect bandgaps of unstrained SixGe1-x-ySny and their photonic device applications. Journal of Applied Physics, 2012, 112, .	2.5	162
57	Electronic states and intraband terahertz optical transitions in InGaAs quantum rods. Journal of Applied Physics, 2012, 111, 073110.	2.5	5
58	Extended density-matrix model applied to silicon-based terahertz quantum cascade lasers. Physical Review B, 2012, 85, .	3.2	38
59	The role of temperature in quantum-cascade laser waveguides. Journal of Computational Electronics, 2012, 11, 137-143.	2.5	8
60	The effects of tensile-strain conditions on doping density requirements for Ge-based injection lasers. , 2011, , .		0
61	Silicon optical modulators for high data rate applications. , 2011, , .		0
62	Design of Ge/SiGe quantum cascade lasers using the density matrix model. , 2011, , .		0
63	Strain engineering of the electroabsorption response in Ge/SiGe multiple quantum well heterostructures. , 2011, , .		0
64	Terahertz sensing and imaging using a quantum cascade laser. , 2011, , .		0
65	Coherent transport description of the dual-wavelength ambipolar terahertz quantum cascade laser. Journal of Applied Physics, 2011, 109, 013111.	2.5	13
66	Magnetotunneling in resonant tunneling structures with spin-orbit interaction. Journal of Applied Physics, 2011, 110, 064507.	2.5	1
67	Plasmonic enhanced electro-optic stub modulator on a SOI platform. Photonics and Nanostructures - Fundamentals and Applications, 2011, 9, 101-107.	2.0	9
68	Demonstration of a self-mixing displacement sensor based on terahertz quantum cascade lasers. Applied Physics Letters, 2011, 99, .	3.3	63
69	Charge Carrier Transport in Quantum Cascade Lasers in Strong Magnetic Field. Acta Physica Polonica A, 2011, 119, 99-102.	0.5	1
70	Inter-Landau Level Scattering Processes in Magnetic Field Assisted THz Quantum Cascade Laser. Acta Physica Polonica A, 2011, 120, 227-230.	0.5	0
71	Dependence of Threshold Current Density on the Waveguide Ridge Width in Quantum-Cascade Lasers. IEEE Journal of Quantum Electronics, 2010, 46, 1320-1326.	1.9	1
72	Phase-breaking effects in double-barrier resonant tunneling diodes with spin-orbit interaction. Journal of Applied Physics, 2010, 108, .	2.5	14

#	ARTICLE	IF	CITATIONS
73	Undertaking research in the field of silicon optical modulators in the framework of the Helios and UK silicon photonics projects. , 2010, , .		0
74	Interdiffusion effects and line broadening of hole intersubband absorption in complex GaAs/AlGaAs quantum well structures. Journal of Applied Physics, 2010, 107, .	2.5	4
75	Design of Ge/SiGe Quantum-Confined Stark Effect Electroabsorption Heterostructures for CMOS Compatible Photonics. Journal of Lightwave Technology, 2010, , .	4.6	17
76	Finite difference method for solving the Schrödinger equation with band nonparabolicity in mid-infrared quantum cascade lasers. Journal of Applied Physics, 2010, 108, .	2.5	59
77	Si/SiGe quantum cascade superlattice designs for terahertz emission. Journal of Applied Physics, 2010, 107, 053109.	2.5	21
78	Ultra-low threshold glass thin film random lasers. , 2010, , .		0
79	Quantum Cascade Laser Design for Tunable Output at Characteristic Wavelengths in the Mid-Infrared Spectral Range. Acta Physica Polonica A, 2010, 117, 772-776.	0.5	1
80	Comparison of SiO <sub>2</sub> , Si <sub>3</sub> N <sub>4</sub> , As <sub>2</sub> S <sub>3</sub> , and Ge <sub>0.25</sub> Se <sub>0.75</sub> dielectric layers for InP- and GaAs-based material systems for midinfrared quantum cascade laser waveguides. Journal of Applied Physics, 2009, 106, 053104.	2.5	5
81	The importance of electron temperature in silicon-based terahertz quantum cascade lasers. Applied Physics Letters, 2009, 95, .	3.3	12
82	Theoretical Modeling of a $\sim 2\text{-}\mu\text{m}$ - $\text{Tm}^{3+}$ -Doped Tellurite Fiber Laser: The Influence of Cross Relaxation. Journal of Lightwave Technology, 2009, 27, 4026-4032.	4.6	20
83	Numerical Rate Equation Modeling of a $\sim 2.1\text{-}\mu\text{m}$ - $\text{Tm}^{3+}/\text{Ho}^{3+}$ Co-Doped Tellurite Fiber Laser. Journal of Lightwave Technology, 2009, 27, 4280-4288.	4.6	36
84	Quantum-confined Stark effect electro-absorption modulators for CMOS compatible photonics. , 2009, , .		0
85	Quantum Dots as Sources and Detectors of Mid- and Far-Infrared Radiation: Theoretical Models. Acta Physica Polonica A, 2009, 116, 464-467.	0.5	9
86	Spin Precession of Quasi-Bound States in Heterostructures with Spin-Orbit Interaction. Acta Physica Polonica A, 2009, 116, 513-515.	0.5	0
87	Electron Transport and Terahertz Gain in Quantum-Dot Cascades. IEEE Photonics Technology Letters, 2008, 20, 129-131.	2.5	18
88	Thermal Modeling of Terahertz Quantum-Cascade Lasers: Comparison of Optical Waveguides. IEEE Journal of Quantum Electronics, 2008, 44, 680-685.	1.9	38
89	SiGe/Si quantum cascade structures deposited by low-energy plasma-enhanced CVD. , 2008, , .		2
90	Mid-infrared quantum cascade laser waveguide losses: An anisotropic complex permittivity model. , 2008, , .		0

#	ARTICLE	IF	CITATIONS
91	Substrate orientation and alloy composition effects in n-type SiGe quantum cascade structures. , 2008, , .		0
92	Electronic structure and optical properties of Sn and SnGe quantum dots. Journal of Applied Physics, 2008, 103, .	2.5	28
93	Time delay in thin slabs with self-focusing Kerr-type nonlinearity. Physical Review A, 2008, 77, .	2.5	16
94	Saturation of intersubband transitions in p-doped GaAs $\hat{\cdot}$ AlGaAs quantum wells. Applied Physics Letters, 2008, 92, .	3.3	10
95	Wide wavelength tuning of GaAs $\hat{\cdot}$ AlxGa1 $\hat{\cdot}$ xAs bound-to-continuum quantum cascade lasers by aluminum content control. Applied Physics Letters, 2008, 92, .	3.3	5
96	Simulated [111] Si $\hat{\cdot}$ SiGe terahertz quantum cascade laser. Applied Physics Letters, 2008, 92, .	3.3	22
97	Spin-dependent dwell times of electron tunneling through double- and triple-barrier structures. Journal of Applied Physics, 2008, 103, 083701.	2.5	7
98	Intervalley Scattering and the Role of Indirect Band Gap AlAs Barriers: Application to GaAs/AlGaAs Quantum Cascade Lasers. Acta Physica Polonica A, 2008, 113, 891-902.	0.5	3
99	Band structure calculations of Si $\hat{\cdot}$ Ge $\hat{\cdot}$ Sn alloys: achieving direct band gap materials. Semiconductor Science and Technology, 2007, 22, 742-748.	2.0	187
100	Interwell relaxation times in p $\hat{\cdot}$ Si $\hat{\cdot}$ SiGe asymmetric quantum well structures: Role of interface roughness. Physical Review B, 2007, 75, .	3.2	32
101	Polyharmonic surface acoustic wave control of single-electron transport in semimetallic carbon nanotubes. Physical Review B, 2007, 76, .	3.2	0
102	Thermal modelling of Antimonide-based quantum cascade lasers. AIP Conference Proceedings, 2007, , .	0.4	0
103	Time Delay in Thin Slabs with Kerr-Type Nonlinearity. Acta Physica Polonica A, 2007, 112, 987-992.	0.5	0
104	A microscopic model of electron transport in quantum dot infrared photodetectors. Journal of Applied Physics, 2006, 100, 074502.	2.5	23
105	Toward Silicon-Based Lasers for Terahertz Sources. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1570-1578.	2.9	30
106	On the incoherence of quantum transport in semiconductor heterostructure optoelectronic devices. International Biennial Baltic Electronics Conference, 2006, , .	0.0	0
107	Influence of doping density on electron dynamics in GaAs $\hat{\cdot}$ AlGaAs quantum cascade lasers. Journal of Applied Physics, 2006, 99, 103106.	2.5	47
108	Investigation of Thermal Effects in Quantum-Cascade Lasers. IEEE Journal of Quantum Electronics, 2006, 42, 857-865.	1.9	52

#	ARTICLE	IF	CITATIONS
109	Influence of injector doping density and electron confinement on the properties of GaAs/Al <sub>0.45</sub> Ga <sub>0.55</sub> As quantum cascade lasers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 411-414.	0.8	4
110	Symmetry based calculation of electronic structure and intraband absorption in GaN/AlN hexagonal quantum dot superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 3939-3942.	0.8	0
111	Theoretical modelling of electron transport in InAs/GaAs quantum dot superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 3770-3773.	0.8	0
112	Lasing in spin-polarized terahertz quantum cascade structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 4401-4404.	0.8	0
113	Electric field domains in p-Si/SiGe quantum cascade structures. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 189-195.	3.0	4
114	Origin of detection wavelength tuning in quantum dots-in-a-well infrared photodetectors. <i>Applied Physics Letters</i> , 2006, 88, 251107.	3.3	20
115	Simulation of a tunable optically pumped terahertz intersubband laser with diluted magnetic semiconductors. <i>Journal of Applied Physics</i> , 2006, 100, 073709.	2.5	13
116	Optically pumped intersublevel MidInfrared lasers based on InAs-GaAs quantum dots. <i>IEEE Journal of Quantum Electronics</i> , 2005, 41, 1361-1368.	1.9	19
117	Optical cavities for Si/SiGe terahertz quantum cascade emitters. <i>Optical Materials</i> , 2005, 27, 851-854.	3.6	4
118	On the Formation of Periodic Electric Field Domains in p-Si/SiGe Quantum Cascade Structures. <i>Journal of Computational Electronics</i> , 2005, 4, 11-14.	2.5	0
119	SUSY transformation of guided modes in semiconductor waveguides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 3552-3555.	0.8	4
120	A physical model of quantum cascade lasers: Application to GaAs, GaN and SiGe devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 980-986.	1.8	14
121	Quantum cascade lasers in magnetic field: An active region model. <i>Physica Status Solidi (B): Basic Research</i> , 2005, 242, 1812-1816.	1.5	2
122	GaAs/Al <sub>0.45</sub> Ga <sub>0.55</sub> As Double Phonon Resonance Quantum Cascade Laser. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	3
123	Temperature dependence of terahertz optical transitions from boron and phosphorus dopant impurities in silicon. <i>Applied Physics Letters</i> , 2005, 87, 101114.	3.3	27
124	Towards automated design of quantum cascade lasers. <i>Journal of Applied Physics</i> , 2005, 97, 084506.	2.5	36
125	Design and simulation of InGaAs <sup>+</sup> AlAsSb quantum-cascade lasers for short wavelength emission. <i>Applied Physics Letters</i> , 2005, 87, 141109.	3.3	6
126	Magnetic-field tunable terahertz quantum well infrared photodetector. <i>Journal of Applied Physics</i> , 2005, 98, 084509.	2.5	15



#	ARTICLE	IF	CITATIONS
127	Silicon quantum cascade lasers for THz sources. , 2005, , .		1
128	Intersubband lifetimes in $\text{Si}^{\delta}\text{-Si}^{\delta}\text{-Si}$ terahertz quantum cascade heterostructures. Physical Review B, 2005, 71, .	3.2	26
129	Carrier Dynamics in Quantum Cascade Lasers. Acta Physica Polonica A, 2005, 107, 75-81.	0.5	0
130	Physical model of quantum-well infrared photodetectors. Journal of Applied Physics, 2004, 96, 269-272.	2.5	31
131	Towards a Si/SiGe Quantum Cascade Laser for Terahertz Applications. Materials Research Society Symposia Proceedings, 2004, 832, 12.	0.1	2
132	Simulation and design of GaN/AlGaIn far-infrared ( $\lambda = 1.34\text{--}1.4\text{m}$ ) quantum-cascade laser. Applied Physics Letters, 2004, 84, 2995-2997.	3.3	83
133	Dilute magnetic semiconductor quantum-well structures for magnetic field tunable far-infrared/terahertz absorption. IEEE Journal of Quantum Electronics, 2004, 40, 1614-1621.	1.9	9
134	Simulation of Carrier Transport in p-Si/SiGe Quantum Cascade Emitters. Journal of Computational Electronics, 2003, 2, 353-356.	2.5	4
135	THz intersubband dynamics in p-Si/SiGe quantum well emitter structures. Physica Status Solidi (B): Basic Research, 2003, 237, 381-385.	1.5	0
136	Mechanisms of temperature performance degradation in terahertz quantum-cascade lasers. Applied Physics Letters, 2003, 82, 1347-1349.	3.3	68
137	Self-consistent scattering model of carrier dynamics in GaAs/AlGaAs terahertz quantum-cascade lasers. IEEE Photonics Technology Letters, 2003, 15, 15-17.	2.5	27
138	Optimal design of GaN/AlGaIn Bragg-confined structures for intersubband absorption in the near-infrared spectral range. IEEE Journal of Quantum Electronics, 2003, 39, 1297-1304.	1.9	13
139	Surface plasmon waveguides with gradually doped or NiAl intermetallic compound buried contact for terahertz quantum cascade lasers. Journal of Applied Physics, 2003, 94, 3249-3252.	2.5	8
140	Intersubband absorption at $\lambda = 1.3\text{--}1.4\text{m}$ in optimized GaN/AlGaIn Bragg-confined structures. Journal of Applied Physics, 2002, 92, 7672-7674.	2.5	7
141	Single-band envelope-function model in the full Brillouin zone for electronic structure calculation in semiconductor nanostructures. Journal of Applied Physics, 2002, 92, 515-522.	2.5	2
142	Self-consistent scattering theory of transport and output characteristics of quantum cascade lasers. Journal of Applied Physics, 2002, 91, 9019-9026.	2.5	129
143	On the interdiffusion-based quantum cascade laser. IEEE Photonics Technology Letters, 2002, 14, 1067-1069.	2.5	0
144	Influence of leakage current on temperature performance of GaAs/AlGaAs quantum cascade lasers. Applied Physics Letters, 2002, 81, 400-402.	3.3	47

#	ARTICLE	IF	CITATIONS
145	Monte Carlo Simulations of Hole Dynamics in Si/SiGe Quantum Cascade Structures. Journal of Computational Electronics, 2002, 1, 191-194.	2.5	5
146	Second harmonic generation at the quantum-interference induced transparency in semiconductor quantum wells: the influence of permanent dipole moments. IEEE Journal of Quantum Electronics, 2001, 37, 873-876.	1.9	6
147	Gain optimization in optically pumped AlGaAs unipolar quantum-well lasers. IEEE Journal of Quantum Electronics, 2001, 37, 1337-1344.	1.9	7
148	Optimization of nonlinear optical rectification in semiconductor quantum wells using the inverse spectral theory. Solid State Communications, 1997, 104, 445-450.	1.9	18
149	Self-consistent rate equation modelling of a Terahertz GaAs/AlGaAs quantum-cascade laser. , 0, , .		0
150	Si /SiGe terahertz quantum cascade emitters. , 0, , .		0
151	In search of a Si/SiGe THz quantum cascade laser. , 0, , .		1
152	Physical Model and Scattering Dynamics Engineering for Intersubband Lasers and Photodetectors. , 0, , .		0
153	Design and optimization of GaN/AlGaN quantum wells and Bragg confined structures for short wavelength ( $1.3\frac{1}{4}\mu\text{m}$ >> $2\frac{1}{4}\mu\text{m}$ ) intersubband absorption. , 0, , .		0
154	LO phonon scattering as a depopulation mechanism in Si/SiGe quantum cascades. , 0, , .		0
155	Terahertz emission and absorption characteristics of silicon containing boron and phosphorous impurity dopants and the effect of temperature. , 0, , .		0